ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089
http://www.nteinc.com

NTE5826 & NTE5827
Power Rectifier Diode, Glass Passivated, 50 Amp, Press Fit

Features:
- Glass Passivated Die Construction
- Low Leakage
- High Surge Current Capability
- Typical I_R less than 5μA
- Rugged Construction
- Available in Standard (NTE5826) and Reverse (NTE5827) Polarity

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%)

Peak Repetitive Reverse Voltage, V_{RRM}
NTE5826, NTE5827* 400V

Working Peak Reverse Voltage, V_{RWM}
NTE5826, NTE5827* 400V

DC Blocking Voltage, V_R
NTE5826, NTE5827* 400V

RMS Reverse Voltage, $V_{R(RMS)}$
NTE5826, NTE5827* 280V

Average Rectified Forward Current (T_C = +150°C), I_O 50A

Non–Repetitive Peak Surge Current, I_{FSM}
(8.3ms Single half Sine–Wave Superimposed on Rated Load) 500A

Forward Voltage (I_F = 50A), V_{FM} 1.0V

Peak Reverse Current (V_R = 400V), I_{RM}
T_A = +25°C 5.0μA
T_A = +100°C 500μA

Typical Junction Capacitance (Note 2), C_J 400pF

Operating Junction Temperature Range, T_J . . . . . –65° to +175°C

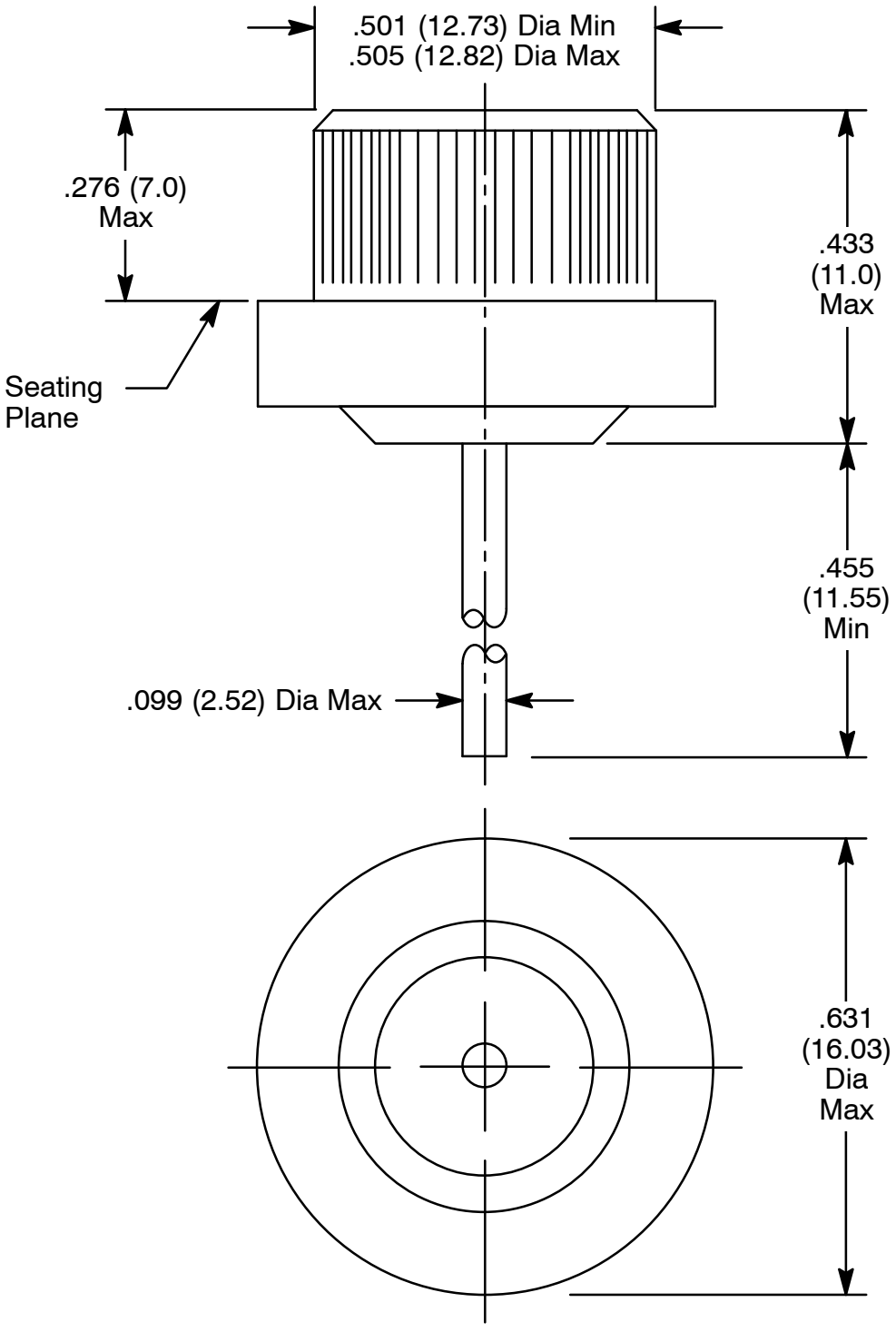
Storage Temperature Range, T_{stg} . . . . . –65° to +175°C

Maximum Thermal Resistance, Junction–to–Case (Note 3), R_{thJC} . . . . . 1.0°C/W

Note 1. Standard polarity is cathode to case, (*) indicated anode to case.
Note 2. Measured at 1.0MHz and applied reverse voltage of 4.0VDC.
Note 3. Thermal Resistance: Junction–to–case, single side cooled.

Rev. 7–19

RoHS


.501 (12.73) Dia Min
.505 (12.82) Dia Max
.276 (7.0)
Max
.433
(11.0)
Max
Seating
Plane
.455
(11.55)
Min
.099 (2.52) Dia Max
.631
(16.03)
Dia
Max